

/ Descriptions

Silicon PNP transistor in a TO-220F Plastic Package.

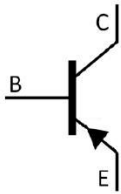
/ Features

Low $V_{CE(sat)}$, High P_C , complementary pair with 2SD2012.

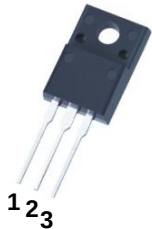
/ Applications

Audio frequency power amplifier applications.

/ Equivalent Circuit



/ Pinning



PIN1 Base PIN 2 Collector PIN 3 Emitter

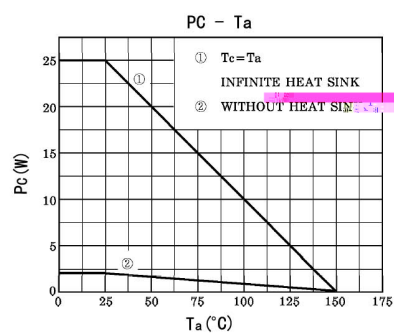
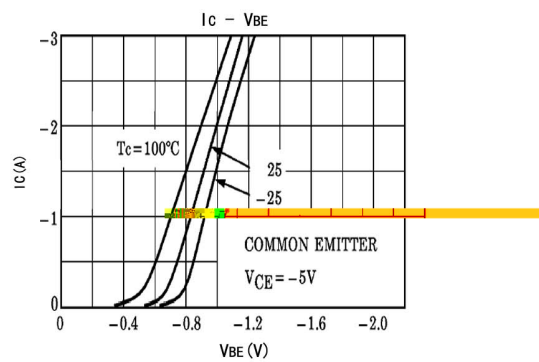
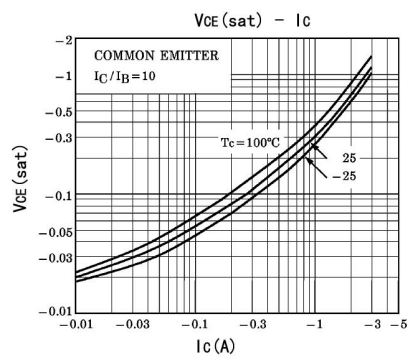
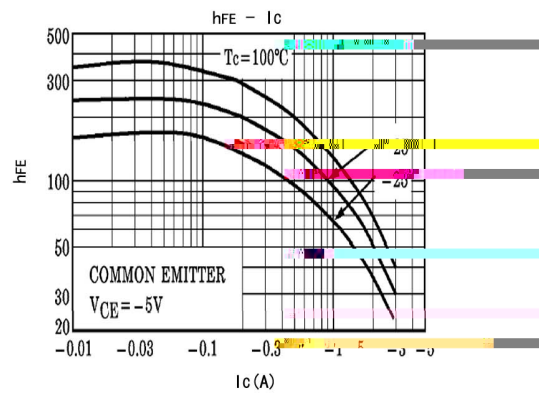
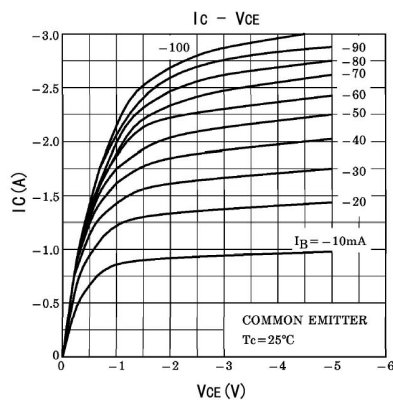
/ h_{FE} Classifications & Marking

See Marking Instructions.

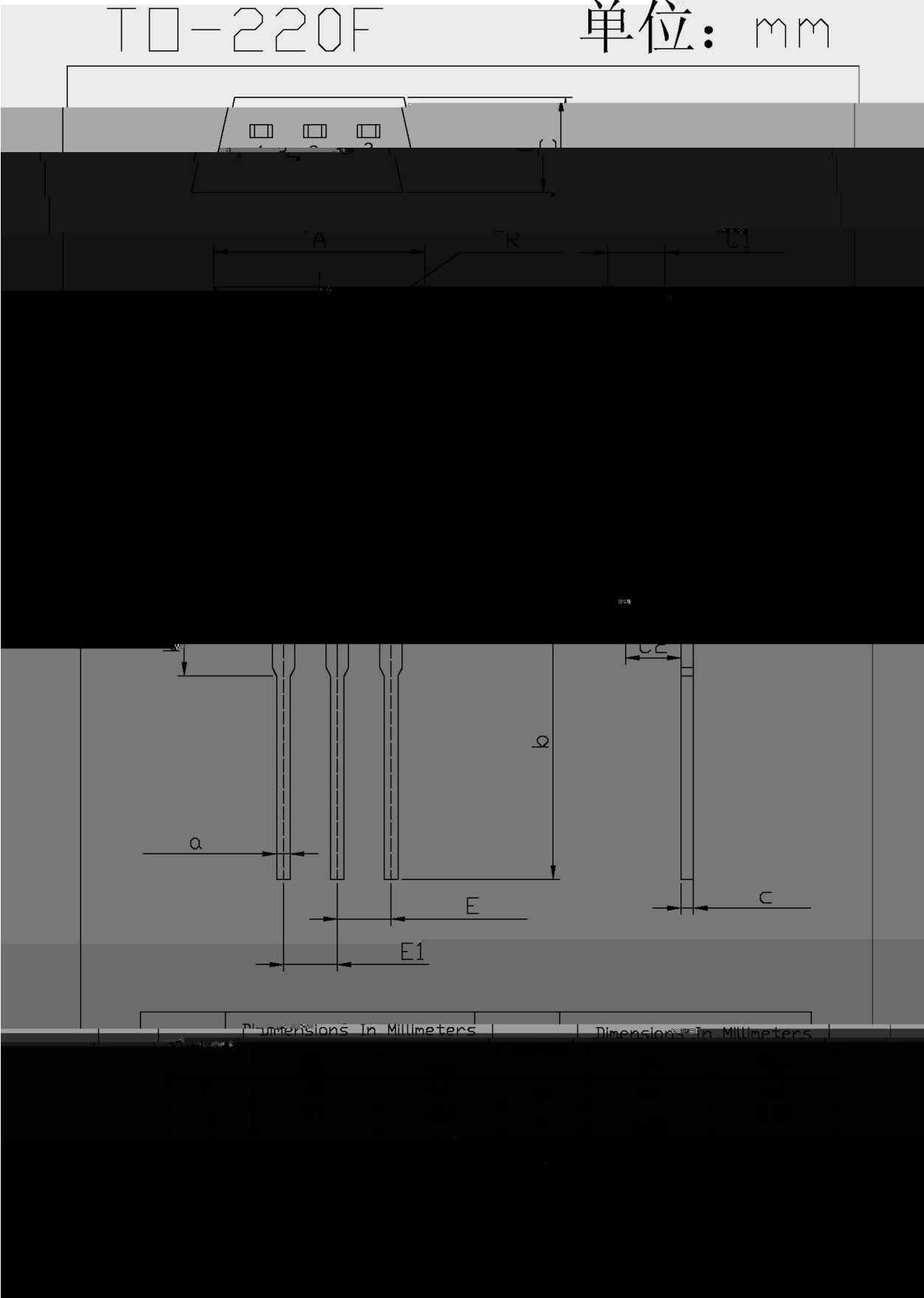
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-60	V
Collector to Emitter Voltage	V_{CEO}	-60	V
Emitter to Base Voltage	V_{EBO}	-7.0	V
Collector Current - Continuous	I_C	-3.0	A
Base Current	I_B	-0.5	A
Collector Power Dissipation	P_C	2.0	W
Collector Power Dissipation	$P_C (T_c=25^{\circ}C)$	25	W
Junction Temperature	T_j	150	$^{\circ}C$
Storage Temperature Range	T_{stg}	-55 150	$^{\circ}C$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-60V \quad I_E=0$			-10	μA
Emitter Cut-Off Current	I_{EBO}	V_{EB}				

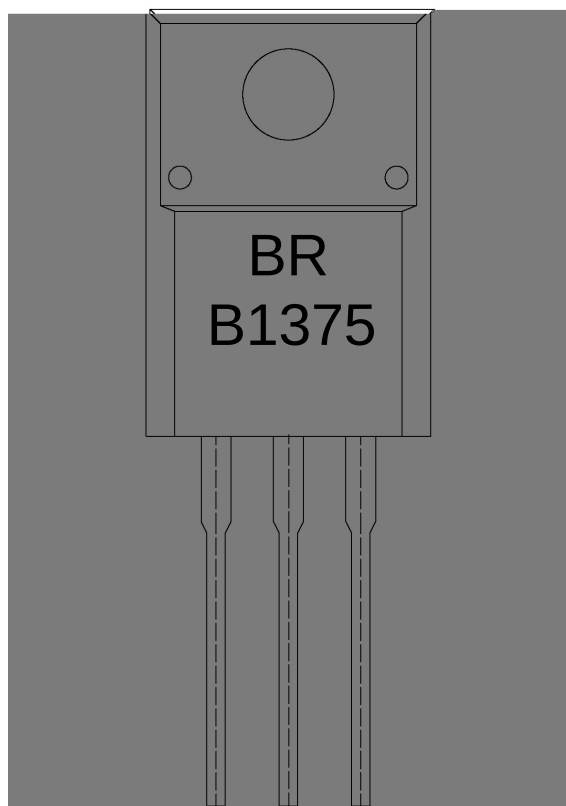
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



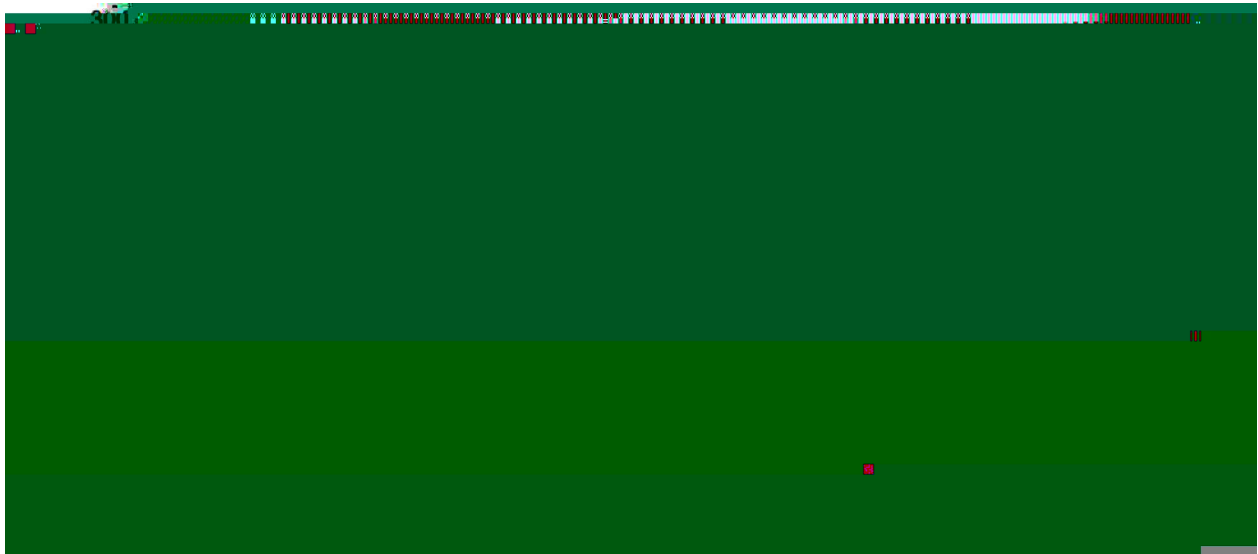
Note:

BR: Company Code.

B1375: Product Type.

***: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- | | | | | | |
|---|-----|-----|----|----------|---|
| 1 | 25 | 150 | 60 | 90sec; | 1.Preheating:25~150 , Time:60~90sec. |
| 2 | 255 | 5 | 5 | 0.5sec; | 2.Peak Temp.:255 5 , Duration:5 0.5sec. |
| 3 | | | 2 | 10 /sec. | 3. Cooling Speed: 2~10 /sec. |

/ Resistance to Soldering Heat Test Conditions

270 5 10 1 sec. Temp.:270±5℃ Time:10±1 sec

/ Packaging SPEC.

/ BULK

Package Type	Units	Dimension	(unit mm ³)
--------------	-------	-----------	-------------------------